

20. The method for making a top electrode for the chamber as recited in claim 18, further comprising:

striking a plasma between the separation, the plasma having a first plasma sheath that is proximate to the wafer surface and a second plasma sheath that outlines an inner region of the top electrode openings, such that the second plasma sheath has an area that is greater than the first plasma sheath.

21. The method for making a top electrode for the chamber as recited in claim 20, further comprising:

increasing an ion bombardment energy over the wafer surface when the second plasma sheath has the area that is greater than the first plasma sheath.

#### REMARKS

Claims 14-21 are pending after entry of this preliminary amendment. Claims 1-13 and 22-32 have been canceled.

The Specification has been amended to correct an error on line 23 of page 13, and is now consistent with the dimensions described on line 4 of the same page.

This preliminary amendment is filed with a divisional of Application Number 09/100,268, filed on June 19, 1998. This divisional is being filed under 37 C.F.R. § 1.53(b), in response to a restriction requirement under 35 U.S.C. § 121. All claims are therefore drawn to the invention of Group II, as designated by the Examiner in telephone conference on November 2, 1999, and in an Office Action dated November 26, 1999.

It is believed that the claims, in their present form, are in a condition for allowance. As such, a notice of allowance is respectfully requested. If the Examiner has any questions concerning the present response, the Examiner is kindly requested to contact the undersigned

06-03-2009

ArPa

### Preliminary Amendment